Amendments to the Claims

1. (CURRENTLY AMENDED) A semiconductor device having opposed first and second major surfaces, comprising:

a body region ~~(4)~~ at the first major surface;

at least one cell ~~(18)~~ having longitudinally spaced source and drain implantations ~~(22, 24)~~ extending into the body region ~~(4)~~ from the first major surface, the source and drain implantations ~~(22,24)~~ being spaced away from the substrate ~~(2)~~ by part of the body region ~~(4)~~ and defining a channel part ~~(40)~~ of the body region ~~(4)~~ between the source and drain implantations; and

at least one insulated gate trench ~~(42)~~ extending longitudinally from the source implantation ~~(22)~~ to the drain implantation ~~(24)~~ through the body region ~~(40)~~, the insulated gate trench ~~(42)~~ including a gate conductor ~~(50)~~ insulated from the source and drain implantations ~~(22,24)~~ and the body region ~~(40)~~ by a gate dielectric ~~(44,46,48,64,66)~~ along the side and end walls and the base of the trench, the source and drain implantations extending along part of the side walls of the trench,

wherein the source and drain implantations ~~(22, 24)~~ include conductive shallow contact regions ~~(26, 28)~~ at the first major surface ,mctending vertic81lly into the body to 81 depth of no rnore than :35% thle, depth of the trench.

2. (ORIGINAL) A semiconductor device according to claim .1 wherein the body region is of first conductivity type and the shallow contact regions are of a second conductivity type opposite to the first conductivity type.

3. (CURRENTLY AMENDED) A semiconductor device according to claim 1 or 2 wherein each of the source and drain implantations ~~(22,24)~~ further comprises a lower doped region ~~(30,32)~~ of lower doping than the shallow contact region.

4. (CURRENTLY AMENDED) A semiconductor device according to claim 3, wherein:

the source implantation ~~(22)~~ includes a higher doped shallow source contact region ~~(26)~~ and a lower doped source drift region (30) between the higher doped source contact region ~~(26)~~ and the body ~~(40)~~;

the drain implantation ~~(24)~~ includes a higher doped shallow drain contact region ~~(28)~~ and a lower doped drain drift region ~~(32)~~ between the higher doped drain contact region ~~(28)~~ and the body ~~(40)~~;

the insulated gate trench ~~(42)~~ includes potential plate regions ~~(60)~~ extending longitudinally on either side of a central region ~~(62)~~, the potential plate regions ~~(60)~~ being adjacent to the source and drain drift regions respectively, and the central region ~~(62)~~ being adjacent to the body; and

the thickness of the gate dielectric sidewalls ~~(64,66)~~ of the insulated gate trench ~~(42)~~ is greater in the potential plate regions ~~(60)~~ of the insulated gate than the central region ~~(62)~~.

5. (CURRENTLY AMENDED) A semiconductor device according to ~~any preceding claim~~claim 1 comprising a plurality of cells ~~(18)~~ laterally spaced across the first major surf81ce.

6. (CURRENTLY AMENDED) A semiconductor device according to claim 5 wherein gate
trenchras ~~(4.2)~~ alternate with Cre;lIs ~~('18)~~ laterally across the surface.

7. A semiconductor device according to claim 5 wherein each cell ~~(18)~~ has a gate trench ~~(42)~~ laterally within the confines of the cell.

8. (CURRENTLY AMENDED) A semiconductor device according to claim 3 wherein the lower doped region ~~(30,32)~~ of lower doping than the shallow contact region extends vertically below the shallow contact region ~~(26,28)~~ to a depth at least 80% of the depth of the trench.

9. (CURRENTLY AMENDED) A semiconductor device according to ~~claim 1 or 2~~claim 1, wherein the source and drain implantations ~~(22, 24)~~ consist exclusively of the shallow contact region ~~(26, 28)~~.

10. (CURRENTLY AMENDED) A semiconductor device according to ~~any preceding claim~~claim 1 on a conductive substrate ~~(2)~~ of first conductivity type.